

# Suck-Whan Kim

## List of Publications by Year in descending order

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12  
papers

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1937685

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1720034

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12  
docs citations

12  
times ranked

52  
citing authors

#	ARTICLE	IF	CITATIONS
1	Growth of AlN layer on patterned sapphire substrate by hydride vapor phase epitaxy. Japanese Journal of Applied Physics, 2016, 55, 05FC02.	1.5	10
2	Thick AlN epilayer grown by using the HVPE method. Journal of the Korean Physical Society, 2015, 67, 643-647.	0.7	7
3	AlN and AlGaIn layers grown on Si(111) substrate by mixed-source hydride vapor phase epitaxy method. Japanese Journal of Applied Physics, 2017, 56, 01AD07.	1.5	5
4	Mechanism of light emission and manufacturing process of vertical-type light-emitting diode grown by hydride vapor phase epitaxy. Japanese Journal of Applied Physics, 2017, 56, 01AD03.	1.5	5
5	Optical property of hexagonal (2H) silicon crystal. Semiconductor Science and Technology, 2021, 36, 095023.	2.0	4
6	Vertical-type Blue Light Emitting Diode by Mixed-Source Hydride Vapor Phase Epitaxy Method. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700491.	1.8	3
7	Growth of AlN Epilayers on Sapphire Substrates by Using the Mixed-Source Hydride Vapor Phase Epitaxy Method. Journal of the Korean Physical Society, 2019, 74, 1160-1165.	0.7	3
8	Insights into the growth of hexagonal Si crystals using Al-based nano absorber. Semiconductor Science and Technology, 2022, 37, 045016.	2.0	2
9	Carbon microspheres grown by using hydride vapor phase epitaxy. Journal of the Korean Physical Society, 2015, 67, 1268-1272.	0.7	0
10	Electrode-Evaporation Method of III-nitride Vertical-type Single Chip LEDs. Journal of the Korean Physical Society, 2018, 73, 1346-1350.	0.7	0
11	Comparison of AlN Nanowire-Like Structures Grown by using Mixed-Source Hydride Vapor Phase Epitaxy Method. Journal of the Korean Physical Society, 2019, 75, 242-247.	0.7	0
12	Growth of a Thick AlN Epilayer by Using the Mixed-Source Hydride Vapor Phase Epitaxy Method. Journal of the Korean Physical Society, 2020, 77, 282-287.	0.7	0